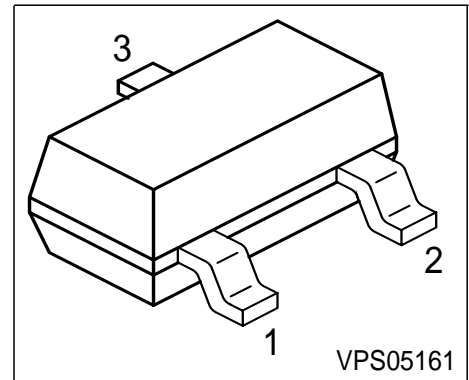**Infineon** technologies

BCW67, BCW68

PNP Silicon AF Transistors

- For general AF applications
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BCW65, BCW66 (NPN)

VPS05161

Type	Marking	Pin Configuration			Package
BCW67A	DAs	1 = B	2 = E	3 = C	SOT23
BCW67B	DBs	1 = B	2 = E	3 = C	SOT23
BCW67C	DCs	1 = B	2 = E	3 = C	SOT23
BCW68F	DFs	1 = B	2 = E	3 = C	SOT23
BCW68G	DGs	1 = B	2 = E	3 = C	SOT23
BCW68H	DHs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	BCW67	BCW68	Unit
Collector-emitter voltage	V_{CEO}	32	45	V
Collector-base voltage	V_{CBO}	45	60	
Emitter-base voltage	V_{EBO}	5	5	
DC collector current	I_C	800		mA
Peak collector current	I_{CM}	1		A
Base current	I_B	100		mA
Peak base current	I_{BM}	200		
Total power dissipation, T_S = 79 °C	P_{tot}	330		mW
Junction temperature	T_j	150		°C
Storage temperature	T_{stg}	-65 ... 150		

Thermal Resistance

Junction - soldering point[1]	R_{thJS}	$\leq$215		K/W

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

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**Electrical Characteristics** at $T_A = 25°C$, unless otherwise specified.

Parameter		Symbol	Values			Unit
			min.	typ.	max.	
DC Characteristics						
Collector-emitter breakdown voltage		$V_{(BR)CEO}$				V
$I_C = 10$ mA, $I_B = 0$	BCW67		32	-	-	
	BCW68		45	-	-	
Collector-base breakdown voltage		$V_{(BR)CBO}$				
$I_C = 10$ µA, $I_B = 0$	BCW67		45	-	-	
	BCW68		60	-	-	
Emitter-base breakdown voltage		$V_{(BR)EBO}$	5	-	-	
$I_E = 10$ µA, $I_C = 0$						
Collector cutoff current		I_{CBO}				nA
$V_{CB} = 32$ V, $I_E = 0$	BCW67		-	-	20	
$V_{CB} = 45$ V, $I_E = 0$	BCW68		-	-	20	
Collector cutoff current		I_{CBO}				µA
$V_{CB} = 32$ V, $I_E = 0$, $T_A = 150$ °C	BCW67		-	-	20	
$V_{CB} = 45$ V, $I_E = 0$, $T_A = 150$ °C	BCW68		-	-	20	
Emitter cutoff current		I_{EBO}	-	-	20	nA
$V_{EB} = 4$ V, $I_C = 0$						
DC current gain 1)		h_{FE}				-
$I_C = 100$ µA, $V_{CE} = 10$ V	h_{FE}-grp.**A/F**		35	-	-	
	h_{FE}-grp.**B/G**		50	-	-	
	h_{FE}-grp.**C/H**		80	-	-	
DC current gain 1)		h_{FE}				
$I_C = 10$ mA, $V_{CE} = 1$ V	h_{FE}-grp.**A/F**		75	-	-	
	h_{FE}-grp.**B/G**		120	-	-	
	h_{FE}-grp.**C/H**		180	-	-	
DC current gain 1)		h_{FE}				
$I_C = 100$ mA, $V_{CE} = 1$ V	h_{FE}-grp.**A/F**		100	160	250	
	h_{FE}-grp.**B/G**		160	250	400	
	h_{FE}-grp.**C/H**		250	350	630	

1) Pulse test: t $\leq$ 300µs, D = 2%

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Electrical Characteristics at T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
DC current gain 1)	h_{FE}				-
I_C = 500 mA, V_{CE} = 2 V $\qquad$ h_{FE}-grp.**A/F**		35	-	-	
h_{FE}-grp.**B/G**		60	-	-	
h_{FE}-grp.**C/H**		100	-	-	
Collector-emitter saturation voltage1)	V_{CEsat}				V
I_C = 100 mA, I_B = 10 mA		-	-	0.3	
I_C = 500 mA, I_B = 50 mA		-	-	0.7	
Base-emitter saturation voltage 1)	V_{BEsat}				
I_C = 100 mA, I_B = 10 mA		-	-	1.25	
I_C = 500 mA, I_B = 50 mA		-	-	2	
AC Characteristics					
Transition frequency	f_T	-	200	-	MHz
I_C = 50 mA, V_{CE} = 5 V, f = 20 MHz					
Collector-base capacitance	C_{cb}	-	6	-	pF
V_{CB} = 10 V, f = 1 MHz					
Emitter-base capacitance	C_{eb}	-	60	-	
V_{EB} = 0.5 V, f = 1 MHz					

Total power dissipation $P_{tot} = f(T_S)$
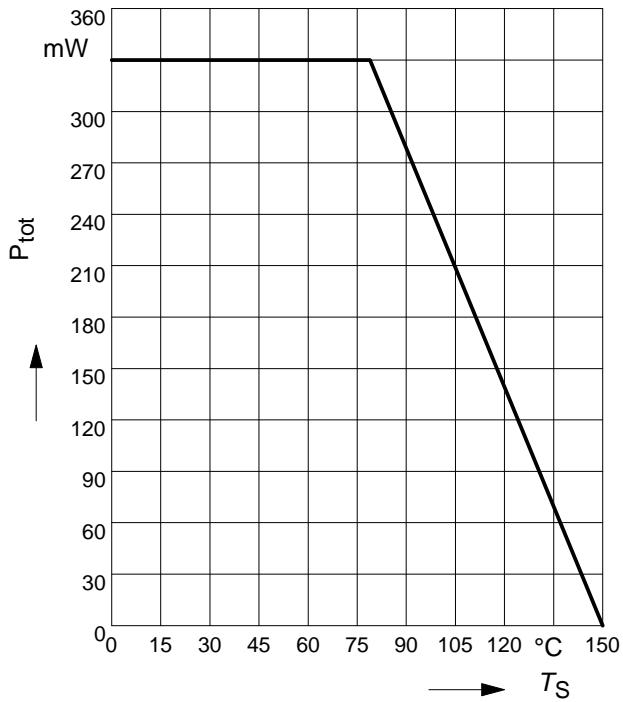
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5V$
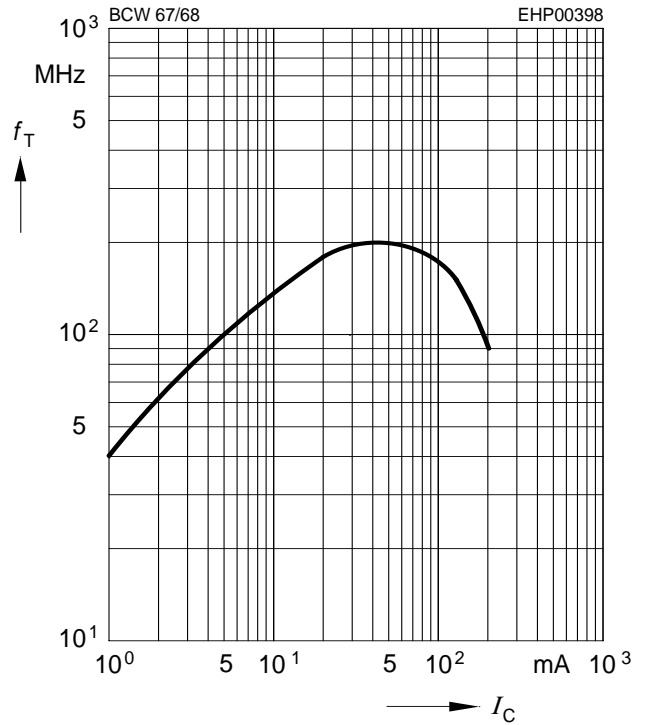
Permissible pulse load

$P_{totmax} / P_{totDC} = f(t_p)$

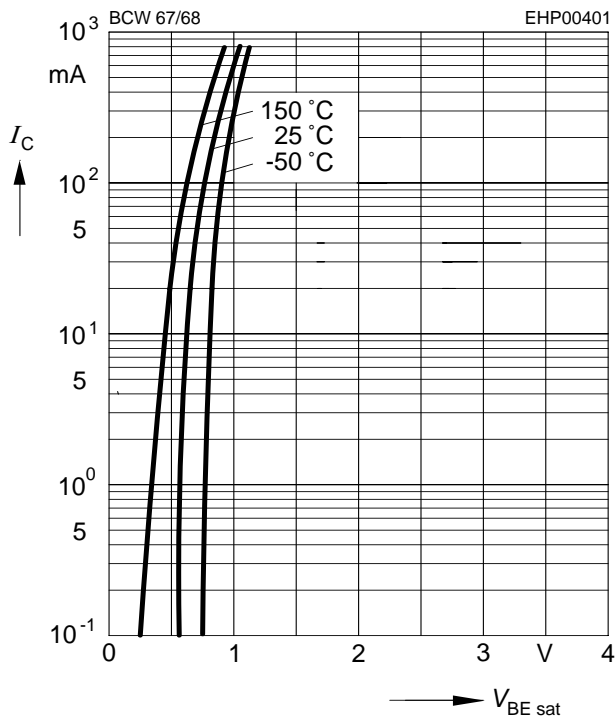$D = \dfrac{t_p}{T}$

$D =$
0
0.005
0.01
0.02
0.05
0.1
0.2
0.5
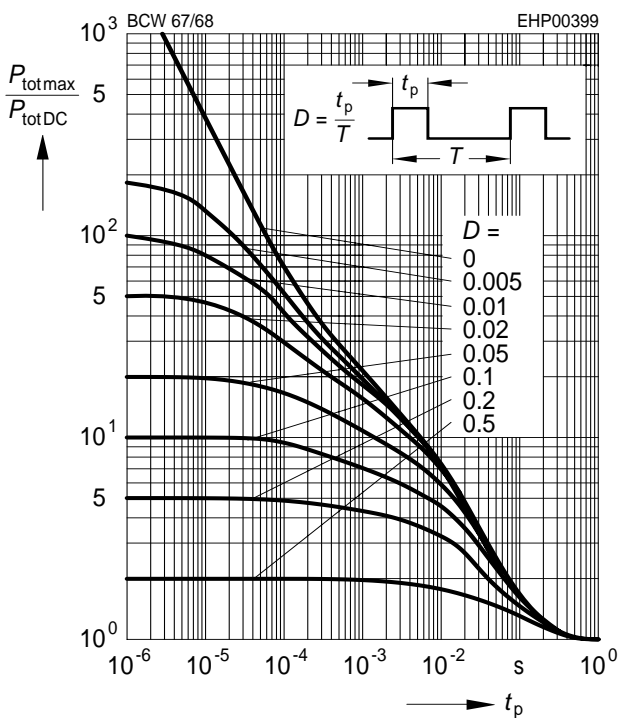
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = V_{CEmax}$
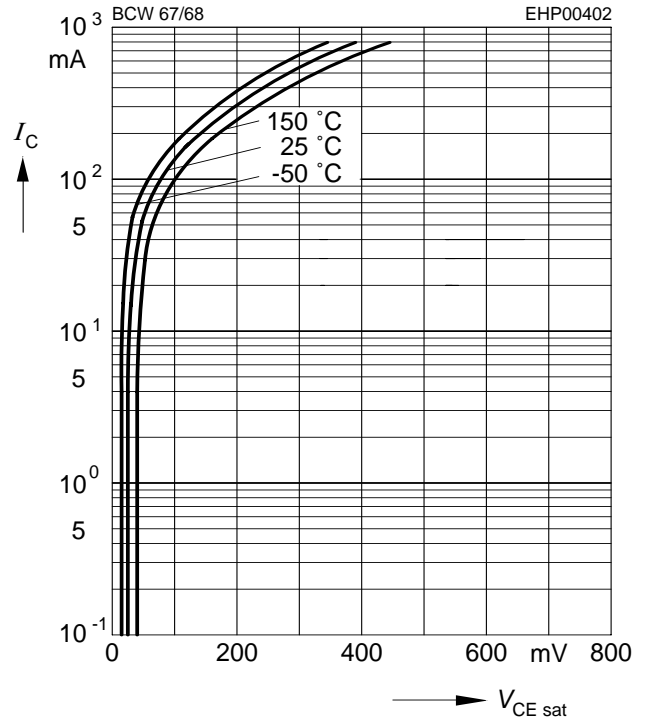
max

typ

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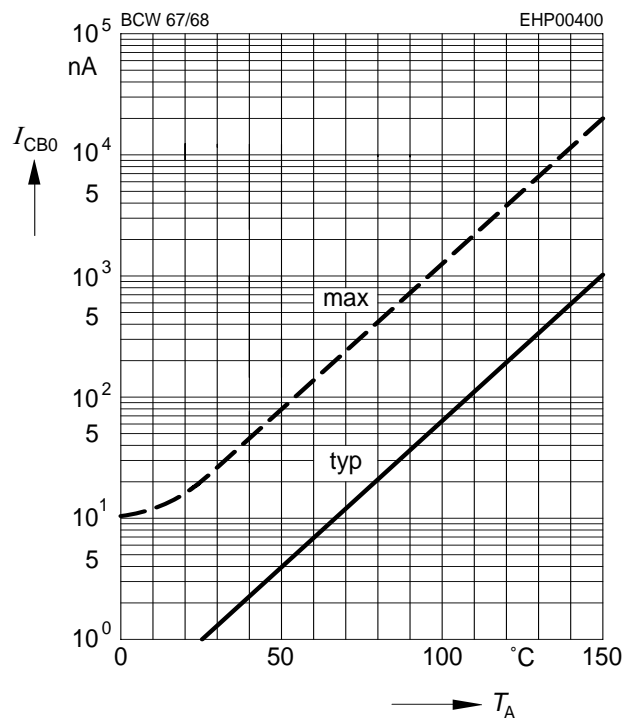
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, $h_{FE} = 10$

Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, $h_{FE} = 10$

DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1V$